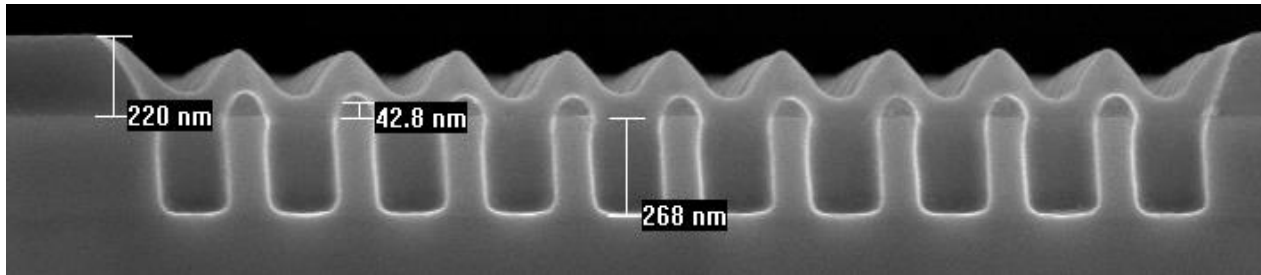


GaAs Nanoscale Etch – ZEP mask

Gas	Flow (sccm)	Pressure (Pa)	Source Pwr. (W)	Bias Pwr. (W)
Cl ₂ /BCl ₃ /Ar	4/3/12	0.35	700	80
Time	Etch depth (nm)	Bulk ZEP Etch Depth (nm)	ZEP Etch Depth on 100nm wide features (nm)	
2'30''	270	230	400	



GaAs Etch Rate:
108nm/min

